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New plant to rise in production capacity for 300-millimeter wafer-cleaning equipment

Dainippon Screen Mfg. Co., Ltd., (headquarters: Kamigyō-ku, Kyoto, Japan; president: Akira Ishida) has finalized plans to build a new plant "Fab. FC1" in the Hikone manufacturing site in Shiga Prefecture. Construction has begun in October 2000, and production is slated to commence in April 2001. Capital investment in the plant is expected to amount to 2 billion yen.

Dainippon Screen develops, manufactures, and markets semiconductor manufacturing equipment used in wafer processing worldwide. The Company's lineup of products includes coater/developers (photoresist coating and developing equipment), single-wafer cleaners and batch-wafer cleaners (wet stations). Currently, Dainippon Screen manufactures these equipment at its Rakusai Plant in Kyoto, and its Yasu, Hikone, and Taga Plant in Shiga Prefecture.

Many semiconductor manufacturers are accelerating their capital investment to attain a substantially larger production capability with strong market's growth. Especially, semiconductor factories for mass production of 300-millimeter wafers, which allow to gain approximately 2.4 times more chips than 200-millimeter wafers, are aim to run in the beginning of 2001 to 2002.

Consequently, Dainippon Screen is expecting the rapid increase in demand for the 300-millimeter wafer-cleaning equipment. The Company already has a keen demand for the equipment, especially after the product has been approved of its reliability by the market. Therefore, Dainippon Screen's primary semiconductor equipment plants are currently operating near capacity with unexpected amount of demand, and facing a sudden needs for expand of production capacity. For the first year the new plant will be producing 100 units of 300-millimeter wafer-cleaning equipment FC-3000* . This enlargement of production site will quadruple the Company's production capacity of 300-millimeter wafer-cleaning equipment, and be aimed at increasing the market share.

The new plant, which will be constructed on a 54,000 square meter site, will be a three-story facility with floor space of approximately 10,000 square meters. Initially, the plant will employ 150 personnel.



Outline of Plant

Location:	Shiga Prefecture
Plant name:	Hikone manufacturing site "Fab. FC1"
Main activities:	Production of semiconductor manufacturing equipment
Construction start:	October 2000
Expected completion:	March 2001
Start of operation:	April 2001
Area of site:	5,400 square meters
Space of building:	4,900 square meters
Total floor space:	10,000 square meters

Note: FC-3000 is the leading edge single bath wafer-cleaning equipment for the next generation 300-millimeter wafer. The FC-3000 is a combination of our best cleaning technologies taken from our multi-bath wet station and the single bath wet station using both concentrated and dilute chemistries. Reducing the space between wafers to half (half-pitch wafer handling system) enables smaller size of bath with maintaining number of wafers to be processed at one time. And also cost of ownership is reduced by the smaller footprint design improving utilization of expensive clean-room space, and also by the decrease in chemical/DI water consumption. Since wafers are not exposed to the air during the cleaning performed in the single bath, they are effectively protected against native oxide growth.